

**Amendments to the Claims**

Listing of Claims:

Claims 1-6 (canceled)

Claim 7 (new): A device for protecting an electronic module ( $\mu$ C, C-T, T2) disposed in a control device (ST) in a multi-voltage on-board electrical system (12V/42V) having an accumulator (BAT1) with a low on-board electrical system voltage ( $V_{bat1}$ ) against short circuiting to a high on-board electrical system voltage, comprising:

a MOSFET transistor (T1) having a drain source path (D-S) inserted between a control device connection (A, A1, A2) and a connection (E, E1, E2) of the electronic module ( $\mu$ C, C-T, T2), and with:

a source (S) connected to the connection (E, E1, E2) of the electronic module ( $\mu$ C, C-T, T2);

a drain (D) connected to the control device connection (A, A1, A2); and

a gate (G);

a Zener diode (D1) connected between said gate (G) and said source (S) of said MOSFET transistor (T1);

a gate resistor ( $R_v$ ) connected between said gate (G) of said MOSFET transistor (T1) and a positive pole ( $+V_{bat1}$ ) of the first accumulator (BAT1); and

a diode (D2) connected in parallel with said gate resistor ( $R_v$ ), for conducting current in a direction from said gate (G) to the positive pole ( $+V_{bat1}$ ) of the accumulator (Bat1).

Claim 8 (new): The device according to claim 7, wherein said electronic module is disposed in control device (ST) for controlling low-power consumers or for processing/transmitting data.

Claim 9 (new): The device according to claim 7, wherein said Zener diode (D1) is configured with a breakdown voltage ( $V_z$ ) lower than a maximum permitted gate

source voltage ( $V_{gs}$ ) of said MOSFET transistor (T1).

Claim 10 (new): The device according to claim 7, wherein said MOSFET transistor (T1) has a threshold voltage ( $V_{th}$ ) and, in an event of a short circuit to a highest voltage of the on-board electrical system active at the device connection (A, A1, A2), a source voltage ( $V_s$ ) of said transistor (T1) is limited to a value  $V_s = V_{bat1} - V_{th}$ , where  $V_s$  is the source voltage,  $V_{bat1}$  is the low on-board voltage ( $V_{bat1}$ ), and  $V_{th}$  is the threshold voltage of said transistor (T1).

Claim 11 (new). The device according to claim 7, wherein, on occurrence of a short circuit to a highest voltage of the on-board electrical system active at the device connection (A, A1, A2), said diode (D2) connected in parallel to said gate resistor ( $R_v$ ) limits the gate voltage ( $V_g$ ) of said MOSFET transistor (T1) to a value  $V_g = V_{bat1} + V_d$ , wherein  $V_g$  is the gate voltage,  $V_{bat1}$  is the low on-board voltage ( $V_{bat1}$ ), and  $V_d$  is a conducting state voltage ( $V_d$ ) of said diode (D2).

Claim 12 (new): The device according to claim 7, with the protective circuit (Ss, Ssa, Ssb) integrated in an ASIC.

Claim 13 (new): The device according to claim 7, wherein the multi-voltage on-board electrical system is a motor vehicle on-board electrical system.